

SUD50N02-06P

Vishay Siliconix

N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^a	
20	0.0060 at V _{GS} = 10 V	26	
20	0.0095 at V_{GS} = 4.5 V	21	

Drain Connected to Tab

TO-252

G D S

Top View

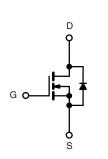
Ordering Information: SUD50N02-06P-E3 (Lead (Pb) free)



- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized for High Efficiency
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 - Desktop
 - Server



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	v
Gate-Source Voltage		V _{GS}	± 20	v
	T _A = 25 °C		26 ^a	
Continuous Drain Current ^a	T _C = 25 °C		50 ^b	
Pulsed Drain Current		I _{DM}	100	А
Continuous Source Current (Diode Conduction) ^a		۱ _S	26	
Avalanche Current	L = 0.1 mH	I _{AS}	45	
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	101	mJ
Maximum Power Dissipation	T _A = 25 °C	P _D	6.8 ^a	w
Maximum Fower Dissipation	T _C = 25 °C		65	v
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum hundling to Angleingtâ	t ≤ 10 s	R _{thJA}	18	22	°C/W
Maximum Junction-to-Ambient ^a	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	1.9	2.3	

Notes:

a. Surface mounted on FR4 board, t \leq 10 s.

b. Limited by package.



1

SUD50N02-06P

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static	1 -		I.	,,,	I I	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.8		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125 °C			1	μA
On-State Drain Current ^b	I _{D(on)}	$v_{DS} = 20 \text{ v}, v_{GS} = 0 \text{ v}, T_{J} = 125 \text{ C}$ $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50		50	A
	D(01)	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0046	0.006	
Drain-Source On-State Resistance ^b	r _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}, \text{ T}_{J} = 125 \text{ °C}$			0.0084	Ω
		V _{GS} = 4.5 V, I _D = 20 A		0.0073	0.0095	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	15			S
Dynamic ^a			•	•		
Input Capacitance	C _{iss}			2550		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$, $V_{DS} = 10 V$, f = 1 MHz		900		
Reverse Transfer Capacitance	C _{rss}			415		
Total Gate Charge ^c	Qg			19	30	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 50 A		7.5		nC
Gate-Drain Charge ^c	Q _{gd}			6		
Gate Resistance	R _g		0.5	1.5	2.4	Ω
Turn-On Delay Time ^c	t _{d(on)}			11	20	
Rise Time ^c	t _r	V_{DD} = 10 V, R_L = 0.2 Ω		10	15	-
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{G}} = 2.5 \Omega$		24	35	ns
Fall Time ^c	t _f			9	15	
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)				
Pulsed Current	I _{SM}				100	А
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, dl/dt = 100 A/μs		35	70	ns

Notes:

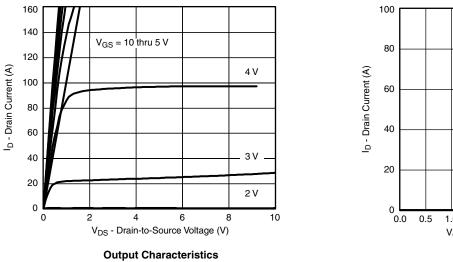
a. Guaranteed by design, not subject to production testing.

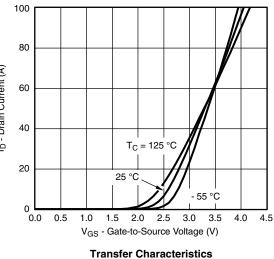
b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)





www.vishay.com 2 Document Number: 71931 S11-2308-Rev. D, 21-Nov-11

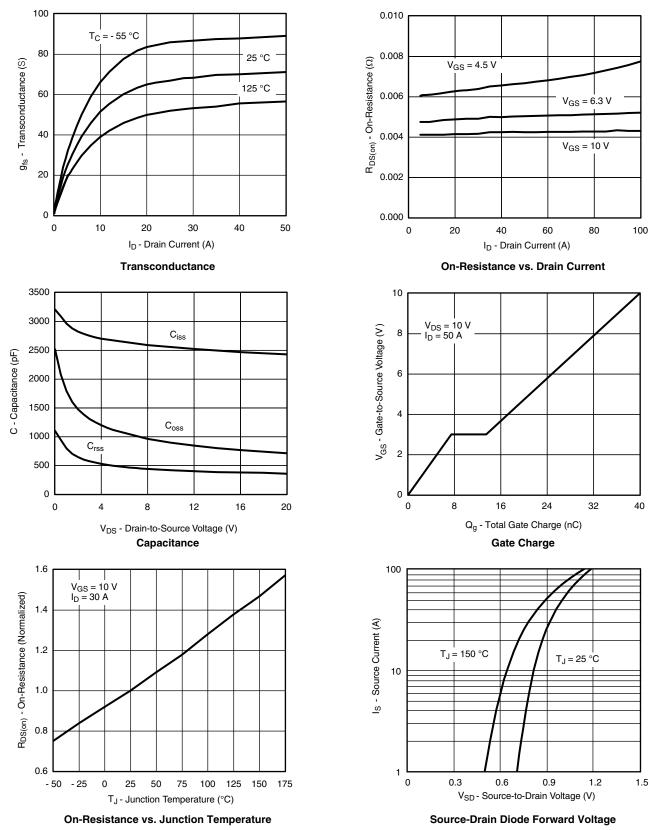
This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



SUD50N02-06P

Vishay Siliconix

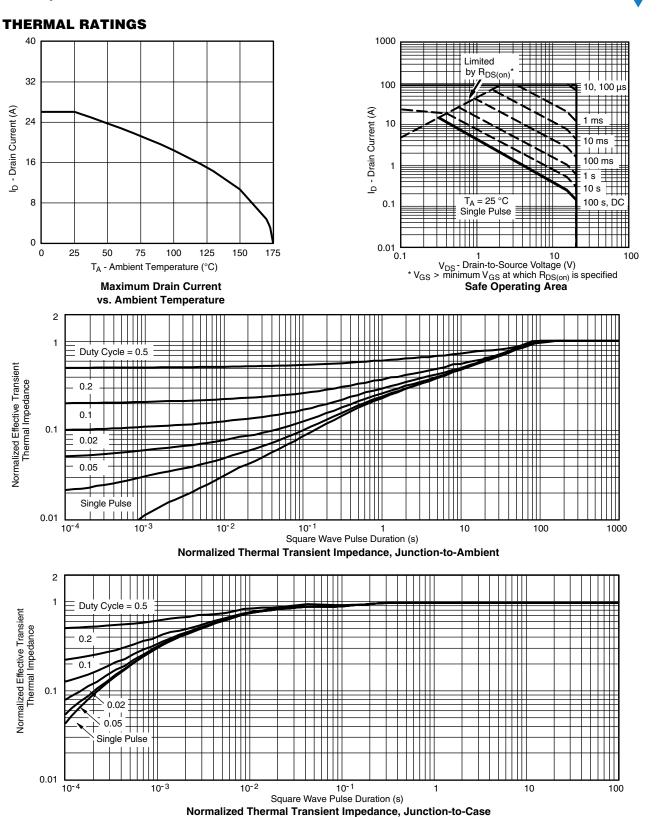
TYPICAL CHARACTERISTICS (25 °C unless noted)



Document Number: 71931 S11-2308-Rev. D, 21-Nov-11 www.vishay.com

3

This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000 Vishay Siliconix



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71931.

www.vishay.com 4 Document Number: 71931 S11-2308-Rev. D, 21-Nov-11

/ISHA

This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

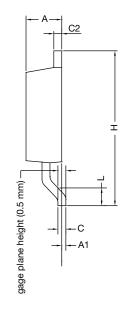


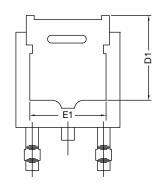


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



Vishay Siliconix

VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
A	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
E	6.35	6.73	
E1	4.32	-	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	l ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

• Dimensioning and tolerance confirm to ASME Y14.5M-1994

• All dimensions are in millimeters. Angles are in degrees

• Heat sink side flash is max. 0.8 mm

Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022 DWG: 5347

2



Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1